

Supporting Information

CdS_xSe_{1-x} Layer-Sensitized TiO₂ Nanowire Array as Efficient Photoelectrode

Tae Kwang Sung, Jun Ha Kang, Dong Myung Jang, Yoon Myung, Gyeong Bok Jung, Han Sung Kim, Chan Su Jung, Yong Jae Cho, Jeunghee Park,* and Chang-Lyoul Lee

Fig. S1: EDX data of the CdS_xSe_{1-x} NWs with (a) $x = 0$, (b) 0.2, (c) 0.4, (d) 0.6, (e) 0.8, and (f) 1; TiO₂-CdS_xSe_{1-x} NCs with (g) $x = 0$, (h) 0.2, (i) 0.4, (j) 0.6, (k) 0.8, and (l) 1. The HAADF STEM images are shown in the insets.

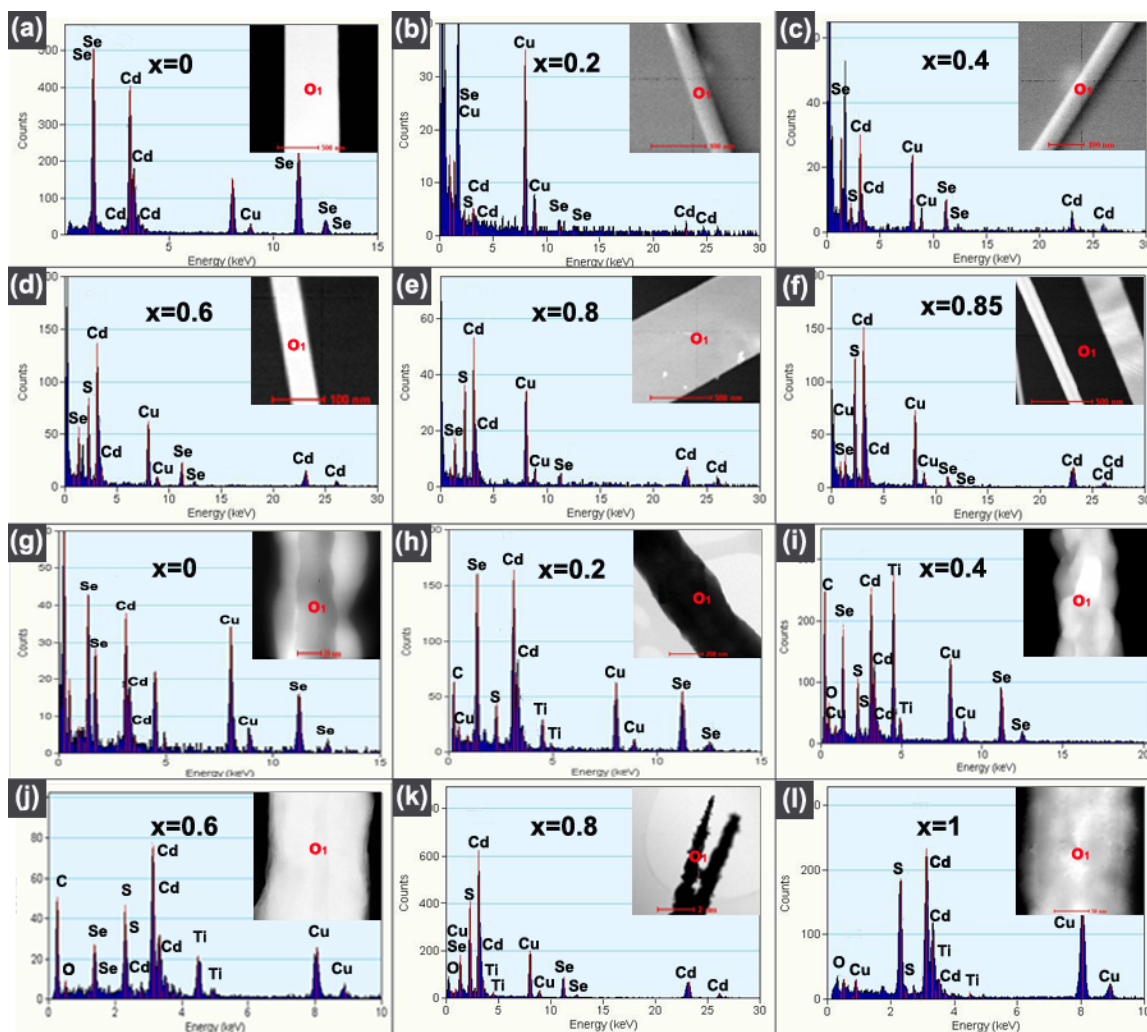


Fig. S2. Band gap of $\text{CdS}_x\text{Se}_{1-x}$ NWs, estimated from Vegard's rule (dotted line), PL, and UV-visible absorption, as a function of S mole fraction (x). It shows the good match of the band gap of the $\text{CdS}_x\text{Se}_{1-x}$ NWs, experimentally determined from the PL band-edge emission, with the predicted E_g values using Vegard's rule (dotted line). The experimental data exhibits a linear fit function, $E_g(x) = 1.74 + 0.73 x$, indicating that there is no bowing effect. For comparison, the band gap, predicted from the onset of the UV-visible absorption band, also follows a linear relation with x , according to $E_g(x) = 1.63 + 0.72 x$.

